

# Boris A Andreev

## List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

122  
papers

876  
citations

15  
h-index

25  
g-index

131  
ext. papers

965  
ext. citations

1.9  
avg, IF

3.38  
L-index

#	Paper	IF	Citations
122	Plasma-Assisted Molecular Beam Epitaxy of In-Rich InGaN: Growth Optimization for Near-IR Lasing. <i>ECS Journal of Solid State Science and Technology</i> , <b>2022</b> , 11, 014003	2	
121	Optical Properties and Upconversion Luminescence of BaTiO <sub>3</sub> Xerogel Structures Doped with Erbium and Ytterbium. <i>Gels</i> , <b>2022</b> , 8, 347	4.2	2
120	Near-infrared stimulated emission from indium-rich InGaN layers grown by plasma-assisted MBE. <i>Applied Physics Letters</i> , <b>2021</b> , 118, 151902	3.4	1
119	Luminescence thermochromism in novel mixed Eu(II)-Cu(I) iodide. <i>Dalton Transactions</i> , <b>2021</b> , 50, 14244-14251	4.3	1
118	Near infrared luminescence of Nd, Er and Yb complexes with perfluorinated 2-mercaptobenzothiazolate and phosphine oxide ligands. <i>Optical Materials</i> , <b>2021</b> , 118, 111241	3.3	1
117	Coherent Radiation From Active Josephson Antennas. <i>IEEE Transactions on Applied Superconductivity</i> , <b>2021</b> , 31, 1-5	1.8	1
116	Ge/Si Core/Shell Quantum Dots in an Alumina Matrix: Influence of the Annealing Temperature on the Optical Properties. <i>Semiconductors</i> , <b>2020</b> , 54, 181-189	0.7	4
115	Effect of antimony doping on the energy of optical transitions in n-Ge layers grown on Si (001) and Ge (001) substrates. <i>Journal of Applied Physics</i> , <b>2020</b> , 127, 165701	2.5	0
114	A Small Cationic Organo-Copper Cluster as Thermally Robust Highly Photo- and Electroluminescent Material. <i>Journal of the American Chemical Society</i> , <b>2020</b> , 142, 373-381	16.4	41
113	Comparative Analysis of the Luminescence of Ge:Sb Layers Grown on Ge(001) and Si(001) Substrates. <i>Semiconductors</i> , <b>2019</b> , 53, 1318-1323	0.7	1
112	Synthesis, structure and long-lived NIR luminescence of lanthanide ate complexes with perfluorinated 2-mercaptobenzothiazole. <i>Dalton Transactions</i> , <b>2019</b> , 48, 1060-1066	4.3	13
111	Features of the Molecular Structure and Luminescence of Rare-Earth Metal Complexes with Perfluorinated (Benzothiazolyl)phenolate Ligands. <i>Molecules</i> , <b>2019</b> , 24,	4.8	3
110	Polynuclear Heteroligand Yb(III)Er(III) Complexes as Potential Upconversion Materials. <i>Russian Journal of Coordination Chemistry/Koordinatsionnaya Khimiya</i> , <b>2019</b> , 45, 712-720	1.6	3
109	Emission Properties of Heavily Doped Epitaxial Indium-Nitride Layers. <i>Semiconductors</i> , <b>2019</b> , 53, 1357-1362	3.7	2
108	Structural and electrical properties of Ge-on-Si(0 0 1) layers with ultra heavy n-type doping grown by MBE. <i>Journal of Crystal Growth</i> , <b>2018</b> , 491, 26-30	1.6	9
107	Towards the indium nitride laser: obtaining infrared stimulated emission from planar monocrystalline InN structures. <i>Scientific Reports</i> , <b>2018</b> , 8, 9454	4.9	15
106	New photoelectrical properties of InN: Interband spectra and fast kinetics of positive and negative photoconductivity of InN. <i>Journal of Applied Physics</i> , <b>2018</b> , 123, 195701	2.5	6

105	LMCT facilitated room temperature phosphorescence and energy transfer in substituted thiophenolates of Gd and Yb. <i>Dalton Transactions</i> , <b>2017</b> , 46, 3041-3050	4.3	27
104	Specific features of the photoexcitation spectra of epitaxial InN layers grown by molecular-beam epitaxy with the plasma activation of nitrogen. <i>Semiconductors</i> , <b>2017</b> , 51, 1537-1541	0.7	
103	Organic Er-Yb complexes as potential upconversion materials. <i>Journal of Luminescence</i> , <b>2017</b> , 192, 208-218	3.8	12
102	Sensitization of NIR luminescence of Yb by Zn chromophores in heterometallic complexes with a bridging Schiff-base ligand. <i>Dalton Transactions</i> , <b>2017</b> , 46, 10408-10417	4.3	16
101	Features of spectral properties of Sm(3+) complexes with dithia- and diselenophosphinate ligands. <i>Spectrochimica Acta - Part A: Molecular and Biomolecular Spectroscopy</i> , <b>2016</b> , 163, 134-9	4.4	12
100	Features of InN growth by nitrogen-plasma-assisted MBE at different ratios of fluxes of group-III and -V elements. <i>Semiconductors</i> , <b>2016</b> , 50, 261-265	0.7	4
99	Exciton self-trapped on SiSi dimers on the surface of silicon nanocrystal: Experimental evidence. <i>Physica Status Solidi (B): Basic Research</i> , <b>2016</b> , 253, 2150-2153	1.3	1
98	Si and Ge nanocrystals in resonator multilayer structures. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2016</b> , 213, 2867-2872	1.6	2
97	Absorption cross section for the $4f^{15} 2 \rightarrow 4f^{13} 2$ transition of Er <sup>3+</sup> in Si:Er:O/SOI epitaxial layers. <i>JETP Letters</i> , <b>2015</b> , 100, 807-811	1.2	2
96	Tris(trifluoromethyl)germylethynyl derivatives of biphenyl and anthracene: Synthesis, structure, and evidence of the intramolecular charge transfer on the germanium center. <i>Journal of Organometallic Chemistry</i> , <b>2015</b> , 797, 83-95	2.3	3
95	Luminescent properties of 2-mercaptobenzothiazolates of trivalent lanthanides. <i>Physical Chemistry Chemical Physics</i> , <b>2015</b> , 17, 11000-5	3.6	13
94	Synthesis and luminescent properties of heteroleptic benzothiazolylbaphtholates of ytterbium. <i>Synthetic Metals</i> , <b>2015</b> , 203, 117-121	3.6	5
93	Deposition of microcrystalline silicon in electron-cyclotron resonance discharge (24 GHz) plasma from silicon tetrafluoride precursor. <i>Thin Solid Films</i> , <b>2014</b> , 562, 114-117	2.2	10
92	Effect of surface Si-Si dimers on photoluminescence of silicon nanocrystals in the silicon dioxide matrix. <i>Journal of Experimental and Theoretical Physics</i> , <b>2014</b> , 118, 728-734	1	5
91	Raman spectra of amorphous isotope-enriched <sup>74</sup> Ge with low-strained Ge nanocrystals. <i>Thin Solid Films</i> , <b>2014</b> , 552, 46-49	2.2	4
90	Lanthanide complexes with substituted naphtholate ligands: extraordinary bright near-infrared luminescence of ytterbium. <i>Russian Chemical Bulletin</i> , <b>2013</b> , 62, 392-397	1.7	19
89	Effect of the annealing temperature on the low-temperature photoluminescence in Si:Er light-emitting structures grown by molecular-beam epitaxy. <i>Semiconductors</i> , <b>2013</b> , 47, 1333-1335	0.7	
88	Towards 0.99999 <sup>28</sup> Si. <i>Solid State Communications</i> , <b>2012</b> , 152, 455-457	1.6	13

87	Luminescent properties of MBE-grown Si:Er/SOI structures. <i>Journal of Luminescence</i> , <b>2012</b> , 132, 3148-3158	0.7	4
86	Determination of the excitation cross section of photoluminescence from an Er ion in the case of homogeneous and inhomogeneous optical excitation. <i>Semiconductors</i> , <b>2012</b> , 46, 1372-1375	0.7	3
85	Mechanism of the subband excitation of photoluminescence from erbium ions in silicon under high-intensity optical pumping. <i>Semiconductors</i> , <b>2012</b> , 46, 1407-1410	0.7	3
84	Dependence of the concentration of ionized donors on epitaxy temperature for Si:Er/Si layers grown by sublimation molecular-beam epitaxy. <i>Semiconductors</i> , <b>2011</b> , 45, 130-133	0.7	2
83	Electroluminescence at a wavelength of 1.54 $\mu\text{m}$ in Si:Er/Si structures consisting of a number of p-n junctions. <i>Semiconductors</i> , <b>2011</b> , 45, 1430-1432	0.7	
82	Electron Mobility in Moderately Doped Si <sub>1-x</sub> Ge <sub>x</sub> . <i>Solid State Phenomena</i> , <b>2011</b> , 178-179, 31-34	0.4	
81	GaAsSb/GaAs strained structures with quantum wells for lasers with emission wavelength near 1.3 $\mu\text{m}$ . <i>Semiconductors</i> , <b>2010</b> , 44, 405-412	0.7	19
80	Specific features of the mechanisms of excitation of erbium photoluminescence in epitaxial Si:Er/Si structures. <i>Semiconductors</i> , <b>2010</b> , 44, 1472-1475	0.7	3
79	Electroluminescence at a wavelength of 1.5 $\mu\text{m}$ in Si:Er/Si diode structures doped with Al, Ga, and B acceptors. <i>Semiconductors</i> , <b>2010</b> , 44, 1597-1599	0.7	
78	Plasma-enhanced chemical vapor deposition of 99.95% <sup>28</sup> Si in form of nano- and polycrystals using silicon tetrafluoride precursor. <i>Crystal Research and Technology</i> , <b>2010</b> , 45, 983-987	1.3	2
77	PECVD growth of crystalline silicon from its tetrafluoride. <i>Crystal Research and Technology</i> , <b>2010</b> , 45, 899-908	1.3	4
76	Electrical properties of Si:Er/Si layers grown by sublimation molecular-beam epitaxy <b>2010</b> , 42, 137		
75	Production of nanocrystalline silicon layers using the plasma enhanced chemical vapor deposition from the gas phase of silicon tetrafluoride. <i>JETP Letters</i> , <b>2009</b> , 89, 73-75	1.2	2
74	Dependence of the energy of the resonance states of an acceptor in silicon on the host isotopic mass. <i>JETP Letters</i> , <b>2009</b> , 90, 455-458	1.2	
73	Band-to-band and direct optical excitation of Er in silicon: Comparison of kinetics, temperature dependence of erbium PL. <i>Physica B: Condensed Matter</i> , <b>2009</b> , 404, 4601-4603	2.8	1
72	Isotopic effects in photoconductivity spectrum of impurities in silicon. <i>Physica B: Condensed Matter</i> , <b>2009</b> , 404, 5057-5059	2.8	1
71	The features of electro-optical memory effect for 1.54 $\mu\text{m}$ electroluminescence of an Er doped Si diode. <i>Physica B: Condensed Matter</i> , <b>2009</b> , 404, 4597-4600	2.8	
70	Isotope-modified silicon layers obtained by plasma enhanced chemical vapor deposition from gaseous silicon tetrafluoride. <i>Technical Physics Letters</i> , <b>2009</b> , 35, 948-950	0.7	

69	Fabrication of nanocrystalline silicon layers by plasma enhanced chemical vapor deposition from silicon tetrafluoride. <i>Semiconductors</i> , <b>2009</b> , 43, 968-972	0.7	4
68	Electrical properties of Si:Er/Si layers grown by sublimation molecular-beam epitaxy. <i>Semiconductors</i> , <b>2008</b> , 42, 137-141	0.7	3
67	Erbium ion electroluminescence in p ++/n +/n-Si:Er/n ++ silicon diode structures. <i>Semiconductors</i> , <b>2007</b> , 41, 1312-1314	0.7	3
66	Erbium doped silicon single- and multilayer structures for light-emitting device and laser applications. <i>Journal of Materials Research</i> , <b>2006</b> , 21, 574-583	2.5	17
65	1.54 $\mu$ m Si:Er light emitting diode with memory function. <i>Applied Physics Letters</i> , <b>2006</b> , 88, 201101	3.4	4
64	Er-Doped Electro-Optical Memory Element for 1.5- $\mu$ m Silicon Photonics. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , <b>2006</b> , 12, 1539-1544	3.8	7
63	Photoluminescence of n-InN with low electron concentrations. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2006</b> , 203, 50-58	1.6	4
62	Acceptor states in the photoluminescence spectra of nInN. <i>Physical Review B</i> , <b>2005</b> , 71,	3.3	128
61	Photoluminescence excitation spectroscopy of erbium in epitaxially grown Si:Er structures. <i>Optical Materials</i> , <b>2005</b> , 27, 890-893	3.3	9
60	Structure, impurity composition, and photoluminescence of mechanically polished layers of single-crystal silicon. <i>Physics of the Solid State</i> , <b>2005</b> , 47, 1	0.8	2
59	Erbium photoluminescence excitation spectroscopy in Si: Er epitaxial structures. <i>Physics of the Solid State</i> , <b>2005</b> , 47, 86	0.8	3
58	Spectroscopic parameters of the absorption bands related to the local vibrational modes of carbon and oxygen impurities in silicon enriched with <sup>28</sup> Si, <sup>29</sup> Si, and <sup>30</sup> Si isotopes. <i>Semiconductors</i> , <b>2005</b> , 39, 300-307	0.7	10
57	Light-emitting Si:Er structures produced by molecular-beam epitaxy: High-resolution photoluminescence spectroscopy. <i>Semiconductors</i> , <b>2005</b> , 39, 1399	0.7	2
56	Manifestation of the equilibrium hole distribution in photoluminescence of n-InN. <i>Physica Status Solidi (B): Basic Research</i> , <b>2005</b> , 242, R33-R35	1.3	6
55	"New Donors" in Czochralski Grown Silicon Annealed at T <sub>600</sub> °C under Compressive Stress. <i>Solid State Phenomena</i> , <b>2005</b> , 108-109, 181-186	0.4	1
54	The Auger process of luminescence quenching in Si/Si:Er multilayers. <i>Journal of Physics Condensed Matter</i> , <b>2005</b> , 17, S2191-S2195	1.8	5
53	Erbium Doped Silicon Single- and Multilayer Structures for LED and Laser Applications. <i>Materials Research Society Symposia Proceedings</i> , <b>2005</b> , 866, 29		
52	Er <sup>3+</sup> photoluminescence excitation spectra in erbium-doped epitaxial silicon structures. <i>Physics of the Solid State</i> , <b>2004</b> , 46, 97-100	0.8	7

51	Effect of growth conditions on photoluminescence of erbium-doped silicon layers grown using sublimation molecular-beam epitaxy. <i>Physics of the Solid State</i> , <b>2004</b> , 46, 101-103	0.8	
50	Erbium and Germanium Profiles in Si <sub>1-x</sub> Ge <sub>x</sub> Layers Grown by Silicon Sublimation-Source Molecular-Beam Epitaxy in GeH <sub>4</sub> . <i>Inorganic Materials</i> , <b>2003</b> , 39, 3-5	0.9	
49	Stress-induced changes of thermal donor formation in heat-treated Czochralski-grown silicon. <i>Physica B: Condensed Matter</i> , <b>2003</b> , 340-342, 769-772	2.8	7
48	Spectroscopic characterization of Er-1 center in selectively doped silicon. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>2003</b> , 105, 150-152	3.1	
47	Infrared lateral photoconductivity of InGaAs quantum dot heterostructures grown by MOCVD. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2003</b> , 17, 634-635	3	8
46	Double thermal donors in Czochralski-grown silicon heat-treated under atmospheric and high hydrostatic pressures. <i>Physica Status Solidi (B): Basic Research</i> , <b>2003</b> , 235, 75-78	1.3	25
45	Study of IR absorption and photoconductivity spectra of thermal double donors in silicon. <i>Physica Status Solidi (B): Basic Research</i> , <b>2003</b> , 235, 79-84	1.3	5
44	Effective cross section for photoluminescence excitation and lifetime of excited Er <sup>3+</sup> ions in selectively doped multilayer Si:Er structures. <i>Semiconductors</i> , <b>2003</b> , 37, 1100-1103	0.7	1
43	Photoluminescence at 1.5 μm from single-crystal silicon layers subjected to mechanical treatment. <i>Semiconductors</i> , <b>2003</b> , 37, 1380-1382	0.7	
42	Smbe Grown Uniformly And Selectively Doped Si:Er Structures For Leds And Lasers <b>2003</b> , 445-454		9
41	Microscopic Structure of Er-Related Optically Active Centers in Si. <i>Materials Research Society Symposia Proceedings</i> , <b>2003</b> , 770, 711		
40	Strain-driven alloying: effect on sizes, shape and photoluminescence of GeSi/Si(001) self-assembled islands. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>2002</b> , 89, 62-65 <sup>21</sup>		16
39	Localised and resonant states of shallow acceptors in Ge/Ge <sub>1-x</sub> Si <sub>x</sub> multiple-quantum well heterostructures. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2002</b> , 13, 317-320	3	1
38	Electrically active centers in Si:Er light-emitting layers grown by sublimation molecular-beam epitaxy. <i>Semiconductors</i> , <b>2002</b> , 36, 171-175	0.7	4
37	Luminescent Si-Ge solid solution layers ER-doped in molecular-beam epitaxy. <i>Semiconductors</i> , <b>2002</b> , 36, 625-628	0.7	2
36	Erbium Segregation in Silicon Layers Grown by Molecular-Beam Epitaxy. <i>Inorganic Materials</i> , <b>2002</b> , 38, 421-424	0.9	
35	Realization of photo- and electroluminescent Si:Er structures by the method of sublimation molecular beam epitaxy. <i>Nanotechnology</i> , <b>2002</b> , 13, 97-102	3.4	14
34	Observation of Zeeman effect in photoluminescence of Er <sup>3+</sup> ion imbedded in crystalline silicon. <i>Physica B: Condensed Matter</i> , <b>2001</b> , 308-310, 340-343	2.8	18

33	Shallow donors in silicon coimplanted with rare-earth ions and oxygen. <i>Physica B: Condensed Matter</i> , <b>2001</b> , 308-310, 350-353	2.8	5
32	Electrically active centers in light emitting Si:Er/Si structures grown by the sublimation MBE method. <i>Physica B: Condensed Matter</i> , <b>2001</b> , 308-310, 361-364	2.8	2
31	Alloy fluctuations in Si <sub>1-x</sub> Ge <sub>x</sub> crystals. <i>Physica B: Condensed Matter</i> , <b>2001</b> , 308-310, 558-560	2.8	
30	Uniformly and selectively doped silicon:erbium structures produced by the sublimation MBE method. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>2001</b> , 81, 67-70	3.1	6
29	Holmium-related luminescence in crystalline silicon. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>2001</b> , 81, 176-178	3.1	3
28	Early stages of oxygen aggregation and thermal donors in silicon annealed under hydrostatic pressure. <i>Journal of Materials Science: Materials in Electronics</i> , <b>2001</b> , 12, 223-225	2.1	5
27	Peculiarities of photoluminescence of erbium in silicon structures prepared by the sublimation molecular-beam epitaxy method. <i>Physics of the Solid State</i> , <b>2001</b> , 43, 1012-1017	0.8	3
26	Simultaneous doping of silicon layers with erbium and oxygen in the course of molecular-beam epitaxy. <i>Semiconductors</i> , <b>2001</b> , 35, 918-923	0.7	3
25	Impact of Compressive Stress on the Formation of Thermal Donors in Heat-Treated Silicon. <i>Solid State Phenomena</i> , <b>2001</b> , 82-84, 259-266	0.4	
24	Thermal Donors in Silicon Implanted with Rare Earth Impurities. <i>Solid State Phenomena</i> , <b>2001</b> , 82-84, 93-98	0.4	2
23	Cyclotron resonance quantum Hall effect detector. <i>Semiconductor Science and Technology</i> , <b>2001</b> , 16, 300-303	1.8	10
22	Properties of optically active Si:Er and Si <sub>1-x</sub> Ge <sub>x</sub> layers grown by the sublimation MBE method. <i>Thin Solid Films</i> , <b>2000</b> , 369, 426-430	2.2	10
21	Shallow acceptors in Ge/GeSi multi-quantum well heterostructures. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2000</b> , 7, 608-611	3	4
20	Shallow acceptors in strained Ge/Ge <sub>1-x</sub> Si <sub>x</sub> heterostructures with quantum wells. <i>Semiconductors</i> , <b>2000</b> , 34, 563-567	0.7	19
19	Doping of silicon layers from a sublimating erbium source in molecular beam epitaxy. <i>Technical Physics Letters</i> , <b>2000</b> , 26, 41-43	0.7	
18	Optical absorption and birefringence in GaAs/AlAs MQW structures due to intersubband electron transitions. <i>Nanotechnology</i> , <b>2000</b> , 11, 218-220	3.4	0
17	Resonant acceptor states in Ge/Ge <sub>1-x</sub> Si <sub>x</sub> MQW heterostructures. <i>Nanotechnology</i> , <b>2000</b> , 11, 348-350	3.4	11
16	Photoluminescence of Erbium-Doped Silicon: Temperature Dependence. <i>Solid State Phenomena</i> , <b>1999</b> , 69-70, 359-364	0.4	2

15	Optically active layers of silicon doped with erbium during sublimation molecular-beam epitaxy. <i>Semiconductors</i> , <b>1999</b> , 33, 131-134	0.7	5
14	Low-temperature photoluminescence in holmium-doped silicon. <i>Semiconductors</i> , <b>1999</b> , 33, 407-409	0.7	1
13	Optical Er-doping of Si during sublimational molecular beam epitaxy. <i>Journal of Crystal Growth</i> , <b>1999</b> , 201-202, 534-537	1.6	25
12	Oxygen aggregation in Czochralski-grown silicon heat treated at 450 °C under compressive stress. <i>Applied Physics Letters</i> , <b>1997</b> , 71, 264-266	3.4	21
11	Donor Centers in Er-Implanted Silicon. <i>Materials Science Forum</i> , <b>1997</b> , 258-263, 1515-1520	0.4	
10	Thermal Donors in Silicon Doped with Erbium. <i>Solid State Phenomena</i> , <b>1997</b> , 57-58, 207-212	0.4	
9	Formation of Thermal Donors in Czochralski Grown Silicon Under Hydrostatic Pressure Up to 1 GPa <b>1996</b> , 345-353		2
8	Silicon as an advanced window material for high power gyrotrons. <i>Journal of Infrared, Millimeter and Terahertz Waves</i> , <b>1995</b> , 16, 863-877		35
7	Oscillator Strengths and Linewidths of Shallow Impurity Spectra in Si and Ge. <i>Materials Science Forum</i> , <b>1995</b> , 196-201, 121-126	0.4	6
6	Copper Species in Ultra-Pure Germanium Crystals. <i>Materials Science Forum</i> , <b>1995</b> , 196-201, 701-706	0.4	
5	Copper in ultra-pure germanium: determination of the electrically active fraction. <i>Semiconductor Science and Technology</i> , <b>1994</b> , 9, 1050-1053	1.8	3
4	Contactless Photothermal Ionization Spectroscopy of Shallow Defects in Semiconductors. <i>Materials Science Forum</i> , <b>1993</b> , 143-147, 1365-1370	0.4	6
3	Submillimeter wave spectrum and molecular constants of N <sub>2</sub> O. <i>Journal of Molecular Spectroscopy</i> , <b>1976</b> , 62, 125-148	1.3	58
2	The metric of submillimeter range of wavelengths using a reference spectrum. <i>Radiophysics and Quantum Electronics</i> , <b>1975</b> , 18, 387-391	0.7	
1	Radiative Properties of Up-Conversion Coatings Formed on the Basis of Erbium-Doped Barium Titanate Xerogels. <i>Semiconductors</i> , 1	0.7	1